

In the Claims:

Please amend the claims as follows:

1. (currently amended) An optoelectronic device, comprising:
a semiconductor substrate;
a photodetector formed adjacent the semiconductor substrate, said photodetector including an AC ground terminal, and a bias terminal; and
a capacitor formed adjacent the semiconductor substrate, wherein said capacitor is coupled between said photodetector AC ground terminal and said photodetector bias terminal, wherein a continuous constant bias is applied to said bias terminal.
2. (original) The optoelectronic device of claim 1 wherein the capacitor comprises an insulator layer formed adjacent to a first electrode and a conductive layer formed adjacent to said insulator layer and overlapping a portion of said first electrode.
3. (original) The optoelectronic device of claim 2 wherein the first electrode comprises a region of conductive semiconductor material.
4. (original) The optoelectronic device of claim 2 wherein the first electrode comprises a metal layer.
5. (original) The optoelectronic device of claim 2 wherein the insulator layer comprises a dielectric layer.
6. (original) The optoelectronic device of claim 5 wherein the dielectric layer comprises silicon nitride.
7. (original) The optoelectronic device of claim 5 wherein the dielectric layer comprises silicon dioxide.
8. (previously amended) The optoelectronic device of claim 2 wherein the insulator layer comprises silicon oxynitride.

9. (original) The optoelectronic device of claim 5 wherein the dielectric layer comprises an organic dielectric.
10. (original) The optoelectronic device of claim 5 wherein the dielectric layer comprises an inorganic dielectric.
11. (original) The optoelectronic device of claim 2 wherein the photodetector comprises a metal-semiconductor-metal detector.
12. (original) The optoelectronic device of claim 2 wherein the photodetector comprises an avalanche photodiode.
13. (original) The optoelectronic device of claim 2 wherein the photodetector comprises a photodiode.
14. (original) The optoelectronic device of claim 13 wherein said photodiode comprises: an intrinsic layer sandwiched between an n-type layer and a p-type layer.
15. (original) The optoelectronic device of claim 14 wherein an isolating implant region is formed in a first portion of said n-type layer.
16. (original) The optoelectronic device of claim 15 wherein said isolating implant region comprises a proton implant region.
17. (previously amended) The optoelectronic device of claim 15 wherein said first electrode comprises a photodetector n-type ohmic contact deposited adjacent said n-type layer, and wherein a second electrode overlaps at least a portion of said first electrode.
18. (original) The optoelectronic device of claim 1 further comprising a bias resistor, wherein said bias resistor couples said photodetector to said bias terminal.
19. (currently amended) An optoelectronic device, comprising:
a semiconductor substrate;
an array of photodetectors formed adjacent the semiconductor substrate; and

one or more monolithic capacitors configured to capacitively couple one or more of the photodetectors to one or more bias terminals, wherein a continuous constant bias is applied to said one or more bias terminals.

20. (original) The optoelectronic device of claim 19 wherein a single monolithic capacitor couples a plurality of said photodetectors to a single bias terminal.

21. (original) The optoelectronic device of claim 19 wherein a plurality of monolithic capacitors couple a plurality of said photodetectors to said one or more bias terminals.

22. (original) The optoelectronic device of claim 19 further comprising one or more bias resistors, wherein said one or more bias resistors couple said one or more photodetectors to said one or more bias terminals.

23. (original) The optoelectronic device of claim 19 wherein a separate monolithic capacitor individually couples each of said one or more photodetectors to said one or more bias terminals.

24. (original) The optoelectronic device of claim 19 further comprising a plurality of monolithic bias resistors, wherein a separate bias resistor is coupled between each of said one or more photodetectors and said one or more bias terminal.

25. (original) The optoelectronic device of claim 19 further comprising a monolithic bias resistor coupled between said one or more photodetectors and a single bias terminal.

26. (original) The optoelectronic device of claim 19 wherein each of said one or more capacitors comprises a dielectric layer formed adjacent to a first electrode and a conductive layer formed adjacent to said dielectric layer and overlapping a portion of said first electrode.

27. (currently amended) The optoelectronic device of claim 22 wherein said one or more bias resistors each comprise a conductive resistor layer formed adjacent a conductive portion of an otherwise highly electrically resistive ~~isolated~~ region.

28. (Canceled)

29. (currently amended) The optoelectronic device of claim 27 wherein said ~~isolated~~ highly electrically resistive region comprises an implant region, and wherein said implant region laterally isolates said conductive resistor layer.

30. (previously amended) An optoelectronic device; comprising:

a multilayered vertical cavity surface emitting laser (VCSEL) formed on a substrate, said VCSEL including a first mirror formed adjacent the substrate, an active region formed adjacent the first mirror, and an second mirror adjacent the active region;

a photodetector formed laterally adjacent to said VCSEL substrate, said photodetector including an AC ground terminal and a bias terminal; and

a capacitor formed on a surface of said photodetector, wherein said capacitor is coupled between a said photodetector AC ground terminal and a said photodetector bias terminal.

31. (original) The optoelectronic device of claim 30 wherein the capacitor comprises a dielectric layer formed adjacent to a first portion of a first electrode and conductive layer formed adjacent to said dielectric layer and overlapping a second portion of said first electrode.

32. (original) The optoelectronic device of claim 30 wherein the photodetector comprises a photodiode.

33. (original) The optoelectronic device of claim 30 wherein the photodetector comprises a metal-semiconductor-metal detector.

34. (original) The optoelectronic device of claim 30 wherein the photodetector comprises an avalanche photodiode.